(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization International Bureau





(43) International Publication Date 9 September 2005 (09.09.2005)

PCT

(10) International Publication Number WO 2005/083809 A1

- (51) International Patent Classification⁷: H01L 41/09, 41/187, 41/24, B41J 2/045, 2/055, 2/16, C01G 25/00, C30B 29/32, H02N 2/00
- (21) International Application Number:

PCT/JP2005/003435

- (22) International Filing Date: 23 February 2005 (23.02.2005)
- (25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data: 2004-055479

27 February 2004 (27.02.2004) JJ

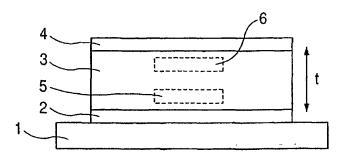
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,

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(54) Title: PIEZOELECTRIC THIN FILM, METHOD OF MANUFACTURING PIEZOELECTRIC THIN FILM, PIEZOELECTRIC ELEMENT, AND INK JET RECORDING HEAD



(57) Abstract: There is disclosed a piezoelectric thin film having less non-uniform portion and holding satisfactory piezoelectric characteristics, a method of manufacturing the film, a piezoelectric element using the piezoelectric thin film, and an ink jet system recording head using the piezoelectric element. In the piezoelectric thin film of perovskite crystals formed on a substrate by a sol-gel process and represented by a general formula Pb $_{(1-x)}$ La_x (Zr_yTi_{1-y}) O₃ (where $0 \le x < 1$, $0.05 \le y \le 1$), a film thickness of the thin film is 1000 nm or more and 4000 nm or less, and a difference between a maximum value and a minimum value of y in an arbitrary portion of the thin film is 0.05 or less.

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